



Fundamentals and Process-Control in Physical Vapor Deposition of Thin Films

Is it possible to design nanomaterials by computer?



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Outline

- Introduction to atomistic processes in thin films grown by vacuum and plasma-assisted PVD techniques
- Fundamentals of Physical Vapor Deposition
 - Without Plasma: electron beam-assisted physical vapor deposition
 - With Plasma: Magnetron sputtering depositions
- Is it possible to design nanomaterials by computer?

Introduction to atomistic processes in thin films grown by vacuum and plasma-assisted PVD techniques

Human technological evolución has been divided in ages



What about now?

Nanotechnology and Plasma Technologies "in the kitchen"



01.- Plasma TV 02.- Coated jet turbine blades 03- Manufactured LEDs in panels 04.- Diamond-like CVD eyeglass coating 05.- Ion-implanted artificial hip 06.- Plasma laser-cut cloth 07.- Plasma HID headlamps $08.-H_2$ in fuel cell 09.- Plasma-aided combustion 10.- Plasma muffler 11.- Plasma ozone water purification 12.- Plasma-deposited LCD screen 13.- Silicon thin films for solar cells 14.- Microelectronics components 15.- Plasma sterilization in pharmaceutical production 16.- Treated Polymers 17.- Treated textiles 18.- Plasma-treated heart stent 19.- Diffusion barriers for containers 20.- Coated window 21.- Compact fluorescent plasma lamp

Processing Techniques in Nanotechnology

Properties of the films are not only determined by the chemical composition but also by <u>the physical structure</u>! We need <u>far from equilibrium situations</u> to grow materials with metastable structures. We do not want <u>EQUILIBRIUM</u>

Control of the film nanostructure in smaller scales

Microelectronics: Moore's Law

Number of Transistor versus years

Transistor gate length versus calendar year

We need to tailor thin film structures in smaller scales

How do we approach the problem? (I)

- Top-Down Strategy
- An overview of the system is formulated.
- Often specified with the assistance of "black boxes".
- Top-down approach starts with the **big picture**.
- Trial and error.

Top-Down Strategy

Pros:

- It leads towards fast results.
- A setup is tuned for maximum efficiency for a given application
- Economically viable
- Good examples that it works in history.

Thomas Edison failed more than 1,000 times when trying to create the light bulb, by trial and error

Edison allegedly said, "I have not failed 1,000 times. I have successfully discovered 1,000 ways to NOT make a light bulb."

<u>Biological evolution</u>: Random mutations and sexual genetic variations can be viewed as trials and poor reproductive fitness as the error. After a long time 'knowledge' of well-adapted genomes accumulates simply by virtue of them being *able* to reproduce

Cons: System-dependent results

- What if we add another element, thus another variable?
- What element do we need to introduce to improve results?
- No causal correlation between input and output
- Do we really control all the variables?
- Protocols at the laboratory could not be straightforwardly up-scaled to mass production.

Look out when correlating data using black boxes!!

It is proved that **butter production in Bangladesh**, U.S. cheese production, and sheep population in **Bangladesh and the U.S.** together "explained" 99% of the annual movements in the stock market in U.S. between 1983 and 1993.¹

Cows really can predict the rain. A theory says that cows can sense increasing air moisture and will plop down to preserve a dry patch of grass. Another theory states that cows lie down to ease their stomachs, which are supposedly sensitive to changes in atmospheric pressure brought on by rainfall. (Daily Mail March 14th 2007)

Cows can't really predict the weather. Cows may lie down before it rains, **but they do that a lot**. Cows lying down in a field more often means **they're chewing their cud**, rather than preparing for raindrops. (NBC News August 20th, 2012)

How do we approach the problem? (II)

Bottom-Up Strategy

- A **bottom-up** approach is the piecing together of systems to give rise to more complex systems.
- Results analyzed as a function of fundamental processes and interaction among subsystems
- Hypotheses and predictions are made: a model is built

Once processes are understood: - Reactor design/modification for desired structures - Open the door to computer design of nanomaterials

Bottom-up Strategy

Pros:

- It gives relevant information from fundamental level
- Allows indentifying the atomistic processes responsable for the nanostructuration
- Permits to design a deposition system to deposit "a la carte" thin films
- Enables computer design of thin films
- Permits process-control and upscaling of laboratory results to industry

Laws of physics (Gravity)

Higgs Boson

. . .

Theory of Relativity

Existence of antimatter

Cons: Complex systems!

- Far from equilibrium
- Non-lineal processes
- Not all processes are known
- Theories are also based on approximations: search of simple conditions

It has also failed in many cases

Graphene does not to exist in the free state, and believed to be unstable with respect to the formation of curved structures.¹

¹Fradkin, E. Critical behavior of disordered degenerate semiconductors, *Phys. Rev. B* **33**, 3263-3268 (1986).

Light propagates in ether

What is a thin film?

Thin Films are very thin layers of materials used to manipulate various surface properties.

Optical thin films (Filters, Anti-reflection, Cosmetic, security devices, architectural)
Surface chemical modification (hydrophobic, bio & chemical sensors)
Barrier coatings (packaging films, ultra-barriers)
Electrical coatings (anti-static, shielding, displays)
Hard and wear resistant coatings (cutting tools, bearings, engine parts, plastic optics)
Decorative coatings (watch cases, bathroom furniture, door furniture, plastic mouldings, metallic yarns

Compact Thin Films

Highly Dense High Refractive Index Low Surface

Porous Thin Films

Low Density Low Refractive Index High Surface Percolation

Control of the structure in smaller scales

Fundamentals of Thin Film Growth (Bottom-Up)

Advances

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Upscaling Protocols to Mass-Production

Scientific Scopes

- General understanding of the physicalchemical processes responsible for film nanostructuration
- Relation between experimentally controllable quantities and film structure
- Connection between structure and properties
- Search of key non-dimensional quantities

Applied scopes

- Development of industrially scalable techniques
- Computer design of materials
- Patents

Fundamentals of physical vapor deposition

Thornton Structure Zone Model

When **T/T_m<0.3**, the film growth is dominated by the surface shadowing mechanism

When **0.3<T/T_m<0.5**, the film growth is dominated by surface shadowing and thermally activated surface mobility processes

Surface Shadowing

- Non-local process
- Depends on the incidence of atoms
- Taller surface features receive more atoms
- Competitive Surface Growth

Competitive Surface Growth

Assume a 2 dimensional problem Particles arriving with incident angle α

E-beam assisted PVD

Atoms arrive along a preferential direction Low kinetic energy of vapor atoms (~0.2 eV)

Development of a model for E-beam assisted PVD

Cross-sectional view Tilted Columnar Structures

Top view Fan-like structures

 $\alpha = 80^{\circ}$ TiO₂ What are the key fundamental quantities? Hypothesis on Growth Model

Results of the Model (I)

 $\alpha = 80^{\circ}$ TiO₂

Cross-sectional view Tilted Columnar Structures **Top view** Fan-like structures

Hypothesis: Angular Broadening

 σ is a system-dependent parameter

Top view Fan-like structures

σ=10°

Surface Trapping Mechanism

 Qualitative Picture

 Slow particles are trapped.

 Fast particles may be trapped or bounced off

 Equilibrium

 position

 Slow particles can be trapped.

 Fast particles may be trapped or not

 Distance particle-surface

S_t trapping probability

Results of the model $S_t=0.1$ $\sigma=6^\circ$

Results are good for TiO2 but, are S_t and σ physical parameters? Is this model good for other materials?

<u>Hypotheses of the model</u> S_t dependent on the sublimated and deposited material

 σ dependent on the deposition system

STRONG (Surface Trapping in Oblique Nanostructured Growths)

www.sincaf-icmse.es

STRONG FEATURES STRONG performs Monte Carlo simulations of the growth of nanostructured thin films deposited by the physical vapor deposition technique at oblique angles. INSTALLATION STRONG requires to have installed the freely distributable MATLAB compiler Runtime (MCR). Once it is installed, open STRONG.exe to start the program. <u>Download MCR</u>

DOWNLOAD

Download STRONG v1.0 Download Manual

Magnetron Sputtering Deposition

- Well-known plasma-assisted
 deposition technique
- High deposition rates
- Possibility to work on large areas
- Room Temperature
- In classical configurations: compact thin films
 - Oblique angle configurations: porous structures

Vacuum Reactor Target	
Substrate	

Difference with e-beam PVD

Sputtered atoms leave the target with energies around 10 eV

Plasma pressure can be tuned, thus sputtered particles may undergo collisions

Mømentum distribution of sputtered particles may vary

- Very directed and along a preferential direction (low collisions in the plasma)
- Isotropic distribution nearly thermalized (high amount of collisions in the plasma)

What happens on the dark side? <u>Cross-Section View</u>

What happens on the dark side? <u>Top View</u>

Isotropic Deposition Growth Mode

What happens on the light side? Thermalization of sputtered particles

The relevance of the **surface shadowing mechanism** makes collisional processes in the **plasma phase** relevant

Thermalization cross-section

Keller-Simmons Formula

 $r = \Phi_0 \frac{p_0 L_0}{pL} \left[1 - \exp\left(-\frac{pL}{p_0 L_0}\right) \right]$

Generalized Keller-Simmons Formula

$$r = \Phi_0 \left(\frac{1}{\delta + \chi} \right) \left[1 + \chi - \left(1 + \chi \right)^{-\delta/\chi} \right]$$
$$\delta = \frac{L}{\lambda_T (L)}, \quad \chi = \frac{T_c}{T_s} - 1$$

$$\lim_{T_c \to T_s} r = \Phi_0 \frac{\lambda_T(L)}{L} \left[1 - \exp\left(-\frac{L}{\lambda_T(L)}\right) \right]$$

KS Formula with $p_0 L_0 = \frac{k_B T_s}{\sigma_T}$

Experimental Data on Deposition Rate

T.P. Drüsedau, Surf. & Coat. Technol. 174-175, 470 (2003)
T.P. Drüsedau, J. Vac. Sci. Technol. A 20(2), 459 (2002)
T.P. Drüsedau, M. Lohmann, and B. Garke, J. Vac. Sci. Technol. A 16(4), 2728 (1998).

	Results of the III									
	P_w (W)	α_0 (atoms m ⁻² s ⁻¹)	α_1 (m ³ J ⁻¹)	α2	T _s (K)	σ (m ²)	T_c (K)	$(p_0 L_0)_{\text{Eq. (3)}}$ (Pa cm)	$(p_0 L_0)_{KS}$ (Pa cm)	
Al	50	$1.8 \times 10^{19} \pm 2 \times 10^{18}$	1.5±0.1	1.0±0.1	370*	$9.6 \times 10^{-20} \pm 6 \times 10^{-21}$	370±40	5.2±0.7	4.6*	
	250	$8 \times 10^{19} \pm 4 \times 10^{18}$	1.5 ± 0.1	1.00 ± 0.03	370 ± 50		370 ± 60	5.2 ± 0.9	4.6*)s
Si	50	$7.5 \times 10^{18} \pm 3 \times 10^{17}$	1.29 ± 0.06	1.15 ± 0.07	373*	$8.3 \times 10^{-20} \pm 4 \times 10^{-21}$	430 ± 30	6.8±0.6	7.5*	P
	250	$3.48 \times 10^{19} \pm 6 \times 10^{17}$	1.03 ± 0.03	1.27 ± 0.05	460 ± 40		590 ± 70	9±1	8.4*	<u>.</u>
V	20	$3.2 \times 10^{18} \pm 10^{17}$	0.75 ± 0.04	1.3 ± 0.1	473*	$6.1 \times 10^{-20} \pm 3 \times 10^{-21}$	610 ± 50	12±1	$14.3 \pm 3^*$	
	200	$3.11 \times 10^{19} \pm 5 \times 10^{17}$	0.78 ± 0.01	1.17 ± 0.04	450 ± 30		530 ± 50	11±1	$12.6 \pm 1^*$	Q
Cr	20	$6.4 \times 10^{18} \pm 2 \times 10^{17}$	0.75 ± 0.03	1.21 ± 0.07	373*	$4.8 \times 10^{-20} \pm 2 \times 10^{-21}$	450 ± 30	12±1	$13.5 \pm 1.8^*$	>
	200	$6.98 \times 10^{19} \pm 7 \times 10^{17}$	0.54 ± 0.01	1.24 ± 0.03	520 ± 30		640 ± 50	17±2	$18.7 \pm 1.2^*$	
Ge	50	$1.53 \times 10^{19} \pm 2 \times 10^{17}$	0.89 ± 0.03	1.14 ± 0.04	470*	$7.2 \times 10^{-20} \pm 2 \times 10^{-21}$	540 ± 20	9.7±0.6	9.4*	
Ta	20	$4.29 \times 10^{18} \pm 7 \times 10^{16}$	0.39 ± 0.01	1.22 ± 0.06	373*	$2.5 \times 10^{-20} \pm 6 \times 10^{-21}$	460 ± 20	23±1	$24.9 \pm 2.9^*$	
W	20	$4.7 \times 10^{18} \pm 10^{17}$	0.42 ± 0.02	1.24 ± 0.09	470*	$3.4 \times 10^{-20} \pm 2 \times 10^{-21}$	580 ± 40	22±2	24*	

$$\lambda_T = \frac{1}{n\sigma_T}, \frac{\lambda_T}{\lambda} = \frac{\sigma}{\sigma_T} \approx \nu$$

 $\frac{L}{\lambda_{T}}$ Thermalization Degree of Sputtered Particles

 $\Xi << 1$ Sputter Flux highly directed Highly Energetic

 $\Xi >> 1$ Sputter Flux thermalized Isotropic momentum distribution Low Energy

Magnetron Sputtering Deposition at Oblique Angles

We analyzed the influence of the tilt angle and the influence of gas pressure

Film was kept far from the (DC) plasma during growth

N.

Percolating Mesopores

R. Álvarez et al. (2012)

E-mail: rafael.alvarez@icmse.csic.es

200 nm

Side View

Isometric View

Top View

Rotating View

Columnar Microstructure

R. Álvarez et al. (2012)

Side View

E-mail: rafael.alvarez@icmse.csic.es

Top View

Isometric View

Is it possible to design nanomaterials by computer?

Approximate information on the nanostructure can be obtained

- Experiments in simple conditions
- Search of key non-dimensional quantities
- Atomistic analysis
- Extrapolation to more technologically-applicable conditions

Computational techniques have been used to predict experimental nanostructures

- Synthesized experimentally
- Under closure (patent)

Important facts to keep in mind

- Using vacuum and plasma-assisted techniques it is possible to grow porous structures.
- Despite the complexity of the phenomenon it is possible to carry out a bottom-up research.
- In simplified conditions it is possible to use computer simulations to design materials
 - Provide experimental conditions to synthesize the desired nanostructures
- Many processes need to be analyzed and fundamental research is necessary (both, from theoretical and experimental points of view)